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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/501,826	07/19/2004	Pradip Mandal	IN 020001	8716
24737	7590 07/13/2005		EXAM	INER
	TELLECTUAL PROP	TRAN, ANH Q		
P.O. BOX 3001 BRIARCLIFF MANOR, NY 10510		ART UNIT	PAPER NUMBER	
BRIARCEIT	William, IVI 10510		2819	

DATE MAILED: 07/13/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

H-W					
	Application No.	Applicant(s)			
Office Action Summany	10/501,826	MANDAL, PRADIP			
Office Action Summary	Examiner	Art Unit			
The MAII INO DATE of this communication on	Anh Q. Tran	2819			
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	orrespondence address			
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be tir y within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from . cause the application to become ABANDONE	mely filed  /s will be considered timely.  the mailing date of this communication.  ED (35 U.S.C. § 133).			
Status	•				
1)⊠ Responsive to communication(s) filed on 19 Ju	<u>uly 2004</u> .				
2a) This action is <b>FINAL</b> . 2b) ⊠ This	This action is <b>FINAL</b> . 2b)⊠ This action is non-final.				
·	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.				
Disposition of Claims					
4) ☐ Claim(s) 1-8 is/are pending in the application. 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-8 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or					
Application Papers					
9)☐ The specification is objected to by the Examine 10)☒ The drawing(s) filed on 19 July 2004 is/are: a)☐ Applicant may not request that any objection to the c Replacement drawing sheet(s) including the correct 11)☐ The oath or declaration is objected to by the Ex	☑ accepted or b)☐ objected to be drawing(s) be held in abeyance. Se ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ejected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. § 119					
12) ☒ Acknowledgment is made of a claim for foreign     a) ☒ All b) ☐ Some * c) ☐ None of:     1. ☐ Certified copies of the priority documents     2. ☐ Certified copies of the priority documents     3. ☒ Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicat rity documents have been receive u (PCT Rule 17.2(a)).	ion No ed in this National Stage			
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 7/19/04.	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:				

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#### **DETAILED ACTION**

## Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 2. Claims 1-2 rejected under 35 U.S.C. 102(e) as being anticipated by Yoshizaki et al (6,194,943).

#### Yoshizaki shows:

- a voltage limiting semiconductor pass gate circuit (Fig. 2), comprising:

  a first transistor (1) being operatively operatively connected between an input

  node (Tin) and an output node (OUT) of the pass gate circuit, the first transistor

  having a control electrode being biased to a supply voltage (Vdd), characterized

  by the control electrode being biased to the supply voltage by two back-to-back

  connected diode elements (8, 9).
- 2. the diode elements are comprised of diode connected transistors.
- 4. An input I/O cell for use with integrated semiconductor circuit, the I/O cell having an input terminal (Tin), an output terminal (Tout) and at least one level detector circuit (7) coupled between the input terminal and the output terminal, characterized by a

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semiconductor pass gate circuit in accordance with claim 1, coupled between the input terminal and the level detector circuit.

- 8. An integrated circuit compromising at least one input I/O cell in accordance with claim 4.
- 3. Claims 1, 2, 3 rejected under 35 U.S.C. 102(e) as being anticipated by Coddington (6,346,829)

Coddington shows:

- a voltage limiting semiconductor pass gate circuit (Fig. 2), comprising:

  a first transistor (111) being operatively operatively connected between an input

  node (1) and an output node (8) of the pass gate circuit, the first transistor having

  a control electrode (2) being biased to a supply voltage (101), characterized by

  the control electrode being biased to the supply voltage by two back-to-back

  connected diode elements (104, 106).
- 2. the diode elements are comprised of diode connected transistors.
- 3. A semiconductor pass gate circuit according to claim 1, wherein the semiconductor pass gate circuit further comprises a second transistor (116) being operatively connected between the input node and the output node, the second transistor having a further control electrode (2) coupled to the control electrode of the transistor via the two back-to-back connected diode elements.

## Claim Rejections - 35 USC § 103

4. Claims 1, 4-8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's Prior Art (Fig. 1) in view of Yoshizaki et al (6,194943).

Applicant's Prior Art shows an I/O circuit (1) comprising: a pass transistor (9), a hysteresis inverter (4), and inverter (5) coupled between an input terminal (2) and output terminal (3). Therefore, the prior art, figure 1, discloses the claimed invention except for a gate of the pass transistor is being biased to the supply voltage by two back-to-back connected diode elements.

Yoshizaki discloses that it is known in the art to provide the gate of the pass transistor with two back-to-back connected diode elements (2 & 4, Fig. 1) biased the supply voltage to it gate. It would have been obvious to one having ordinary skill in the art at the time the invention was made to provide the gate of the pass transistor of the Applicant prior art with the two back-to-back connected diode elements of Yoshizaki, in order to prevent the input circuit of a voltage exceeding the break-down voltage of the gate oxide film of a transistor even if the circuit receives a high-voltage signal, and suppressing the increase in propagation delay even with a reduced power supply voltage.

### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Anh Q. Tran whose telephone number is 571-272-1813. The examiner can normally be reached on M-TH (7:00-5:30) Friday off.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Tokar can be reached on 571-272-1812. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

ANH Q.TRAN
PRIMARY EXAMINER

7/8/05